

Free-running, room temperature operation of an InGaAs/InP single-photon avalanche diode

Ryan E. Warburton,^{1,a)} Mark Itzler,² and Gerald S. Buller¹

of passive quenching, as described in detail in Ref. [12](#), in

gated Geiger-mode measurements were not performed at temperatures above 250 K due to the increased DCR.

We also examined how the gain of the SPAD in this quenching mode changed with voltage to examine the toler-